



## RF TRANSISTOR SELECTOR GUIDES

### SMALL-SIGNAL TRANSISTORS

(Listed in order of operating test frequency and power gain)

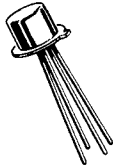
Type	Material	Polarity	f MHz	Min $G_{pe}$ (dB) Min $P_{out}$ (mW)* Typ Conversion Gain (dB)†
2N3324	Ge	P	10	24
2N2273	Ge	P	30	10
2N741, A	Ge	P	30	16
2N2929	Ge	P	60	26
2N700	Ge	P	70	20
2N700A	Ge	P	70	22
2N3323	Ge	P	100	11
2N707, A	Si	N	100	200*
2N1562	Ge	P	160	5.0
2N1693	Ge	P	160	5.0
2N1561	Ge	P	160	6.0
2N1692	Ge	P	160	6.0
MM1941	Si	N	175	7.0
2N4072, 3	Si	N	175	10
2N3286	Ge	P	200	14
2N3294	Si	N	200	14
2N918	Si	N	200	15
2N2708	Si	N	200	15
2N3281	Ge	P	200	16
2N3282	Ge	P	200	16
2N3283	Ge	P	200	16
2N3284	Ge	P	200	16
2N3291, 2	Si	N	200	16
2N3127	Ge	P	200	17
2N3279, 80	Ge	P	200	17
2N3287 thru 90	Si	N	200	17
2N3307, 8	Si	P	200	17
2N3785	Ge	P	200	18
2N3783, 4	Ge	P	200	20
MM5002	Ge	P	200	20
MM5001	Ge	P	200	22
MM5000	Ge	P	200	24
2N3137	Si	N	250	6.0
MM1803	Si	N	250	7.5
2N2857	Si	N	450	12.5
2N3839	Si	N	450	12.5
2N4959	Si	P	450	15
2N4958	Si	P	450	16
2N4957	Si	P	450	17
2N1141, 2, 3	Ge	P	500	10 typ
2N1195	Ge	P	500	10 typ
AF239	Ge	P	800	11.2 G
2N3544	Si	N	1000	10*
MM1501	Si	N	1500	150*
MM1500	Si	N	1500	250*
MM380	Ge	P	1500 $f_{max}$	
MM1139	Ge	P	108 to 10.7	22†

**JAN 2N3127 (GERMANIUM)**

**$V_{CEO} = 20\text{ V}$   
 $I_C = 50\text{ mA}$   
 $P_D = 100\text{ mW}$**

**2N3127**

**CASE 20**  
(TO-72)



PNP germanium mesa transistors designed for industrial and commercial VHF/UHF amplifier applications, and qualified to meet the requirements of MIL-S-19500/346 EL.

Active Elements Isolated From Case

**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	20	Vdc
Collector-Emitter Voltage	$V_{CES}$	25	Vdc
Collector-Base Voltage	$V_{CB}$	25	Vdc
Emitter-Base Voltage	$V_{EB}$	0.75	Vdc
Collector Current	$I_C$	50	mA <sub>dc</sub>
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	100 1.33	mW mW/ $^\circ\text{C}$
Operating & Storage Junction Temperature	$T_J, T_{stg}$	-65 to +100	$^\circ\text{C}$